

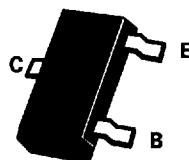
SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 3 - FEBRUARY 1996

BCX17 BCX18

PARTMARKING DETAILS - BCX17 - T1
BCX18 - T2
BCX17R - T4
BCX18R - T5

COMPLEMENTARY TYPES - BCX17 - BCX19
BCX18 - BCX20



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	BCX17	BCX18	UNIT
Collector-Emitter Voltage	V_{CES}	-50	-30	V
Collector-Emitter Voltage ($I_C = -10mA$)	V_{CEO}	-45	-25	V
Emitter-Base Voltage	V_{EBO}	-5		V
Collector Current	I_C	-500		mA
Peak Collector Current	I_{CM}	-1000		mA
Base Current	I_B	-100		mA
Peak Base Current	I_{BM}	-200		mA
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	330		mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150		$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	I_{CBO}			-100 -200	nA μA	$I_E = 0, V_{CB} = -20V$ $I_E = 0, V_{CB} = -20V, T_j = 150^\circ C$
Emitter-Base Cut-Off Current	I_{EBO}			-10	μA	$I_C = 0, V_{EB} = -1V$
Base-Emitter Voltage	V_{BE}			-1.2	V	$I_C = -500mA, V_{CE} = -1V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-620	mV	$I_C = -500mA, I_B = -50mA^*$
Static Forward Current Transfer Ratio	h_{FE}	100 70 40		600		$I_C = -100mA, V_{CE} = -1V$ $I_C = -300mA, V_{CE} = -1V^*$ $I_C = -500mA, V_{CE} = -1V^*$
Transition Frequency	f_T		100		MHz	$I_C = -10mA, V_{CE} = -5V$ $f = 35MHz$
Collector - base Capacitance	C_{obo}		8.0		pF	$I_E = I_C = 0, V_{CB} = -10V$ $f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device